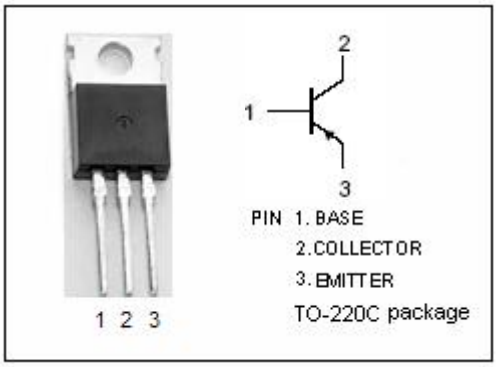
isc Silicon PNP Power Transistor — 2SB526

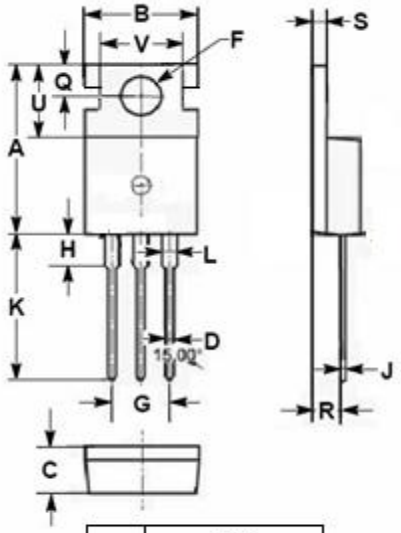


DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -80V(Min)
- Good Linearity of h_{FE}
- Complement to Type 2SD356
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for AF high power dirver applications.



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-90	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-0.8	A
P_C	Collector Power Dissipation @ T_a=25℃	1	W
	Collector Power Dissipation @ T_C=25℃	10	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

isc Silicon PNP Power Transistor 2SB526

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA; R_{BE}= ∞	-80			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -1mA; I_E= 0	-90			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -1mA; I_C= 0	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -0.3A; I_B= -30mA			-1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -50mA; V_{CE}= -4V		0.7		V
I_{CEO}	Collector Cutoff Current	V_{CE}= -80V; R_{BE}= ∞			-1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-10	μA
h_{FE}	DC Current Gain	I_C= -0.3A; V_{CE}= -4V	55		300	

◆ **h_{FE} Classifications**

C	D	E
55-110	90-180	150-300